Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors

Annular PNPN devices designed for high volume consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-92/TO-226AA package which is readily adaptable for use in automatic insertion equipment.

Features

- Sensitive Gate Trigger Current 200 μA Maximum
- Low Reverse and Forward Blocking Current 50 μA Maximum, $T_{C} = 110^{\circ}C$
- Low Holding Current 5 mA Maximum
- Passivated Surface for Reliability and Uniformity
- These are Pb-Free Devices

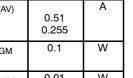
MAXIMUM RATINGS (T1 = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) $(T_J = -40 \text{ to } 110^\circ\text{C}, \text{Sine Wave}, \text{S0 to } 60 \text{ Hz}, \text{R}_{\text{GK}} = 1 \text{ k}\Omega)$ 2N5060 2N5061 2N5062 2N5064 2N5064	V _{DRM,} V _{RRM}	30 60 100 200	V
On-State Current RMS (180° Conduction Angles; $T_C = 80$ °C)	I _{T(RMS)}	0.8	A
*Average On-State Current (180° Conduction Angles) $(T_C = 67^{\circ}C)$ $(T_C = 102^{\circ}C)$	I _{T(AV)}	0.51 0.255	A
*Peak Non-repetitive Surge Current, $T_A = 25^{\circ}C$ (1/2 cycle, Sine Wave, 60 Hz)	I _{TSM}	10	A
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	0.4	A ² s
*Average On-State Current (180° Conduction Angles) $(T_{C} = 67^{\circ}C)$ $(T_{C} = 102^{\circ}C)$	I _{T(AV)}	0.51 0.255	A
*Forward Peak Gate Power (Pulse Width \leq 1.0 µsec; T _A = 25°C)	P _{GM}	0.1	W
*Forward Average Gate Power $(T_A = 25^{\circ}C, t = 8.3 \text{ ms})$	P _{G(AV)}	0.01	W
*Forward Peak Gate Current (Pulse Width \leq 1.0 µsec; T _A = 25°C)	I _{GM}	1.0	A
*Reverse Peak Gate Voltage (Pulse Width \leq 1.0 µsec; T _A = 25°C)	V _{RGM}	5.0	V
*Operating Junction Temperature Range	TJ	-40 to +110	°C
*Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*Indicates JEDEC Registered Data.

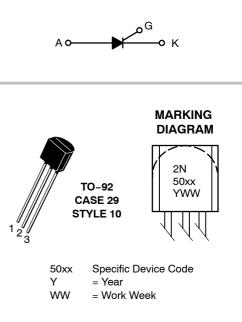




ON Semiconductor®

http://onsemi.com

SILICON CONTROLLED RECTIFIERS 0.8 A RMS, 30 - 200 V



PIN ASSIGNMENT			
1	Cathode		
2	Gate		
3	Anode		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction-to-Case (Note 2)	$R_{ hetaJC}$	75	°C/W
Thermal Resistance, Junction-to-Ambient		200	°C/W

2. This measurement is made with the case mounted "flat side down" on a heatsink and held in position by means of a metal clamp over the curved surface.

*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

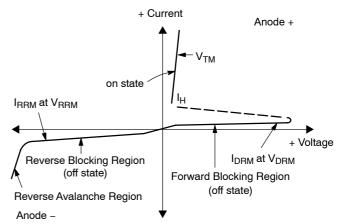
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
*Peak Repetitive Forward or Reverse Blocking Current (Note 3) (V _{AK} = Rated V _{DRM} or V _{RRM}) $T_C = 25^{\circ}C$ $T_C = 110^{\circ}C$	I _{DRM} , I _{RRM}			10 50	μΑ μΑ
ON CHARACTERISTICS	•				•
*Peak Forward On–State Voltage (Note 4) (I _{TM} = 1.2 A peak @ T _A = 25°C)	V _{TM}	-	-	1.7	V
$ \begin{array}{l} \mbox{Gate Trigger Current (Continuous DC) (Note 5)} \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	I _{GT}			200 350	μA
$ \begin{array}{ll} \mbox{Gate Trigger Voltage (Continuous DC) (Note 5)} & T_C = 25^\circ C \\ \mbox{*}(V_{AK} = 7.0 \mbox{ Vdc}, \mbox{ R}_L = 100 \ \Omega) & T_C = -40^\circ C \end{array} $	V _{GT}		-	0.8 1.2	V
*Gate Non-Trigger Voltage (V_{AK} = Rated V_{DRM} , R_L = 100 Ω) T_C = 110°C	V _{GD}	0.1	_	_	V
	Iн		-	5.0 10	mA
Turn-On Time Delay Time Rise Time $(I_{GT} = 1.0 \text{ mA}, V_D = \text{Rated } V_{DRM},$ Forward Current = 1.0 A, di/dt = 6.0 A/ μ s	t _d t _r	-	3.0 0.2		μs
Turn-Off Time (Forward Current = 1.0 A pulse, Pulse Width = 50 μ s, 0.1% Duty Cycle, di/dt = 6.0 A/ μ s, dv/dt = 20 V/ μ s, I _{GT} = 1 mA) 2N5060, 2N5061 2N5062, 2N5064	tq	_	10 30	_	μs

Critical Rate of Rise of Off–State Voltage (Rated V_{DRM} , Exponential, R_{GK} = 1 k Ω)	dv/dt	-	30	-	V/µs]
--	-------	---	----	---	------	---

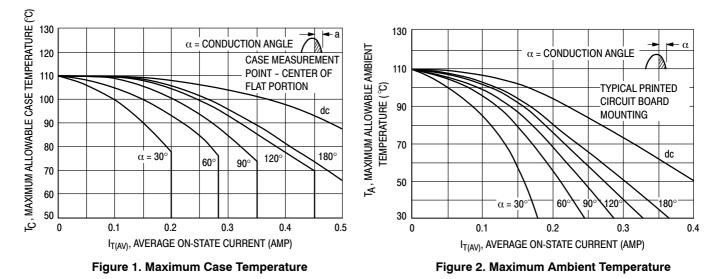
*Indicates JEDEC Registered Data. 3. $R_{GK} = 1000 \Omega$ is included in measurement. 4. Forward current applied for 1 ms maximum duration, duty cycle \leq 1%. 5. R_{GK} current is not included in measurement.

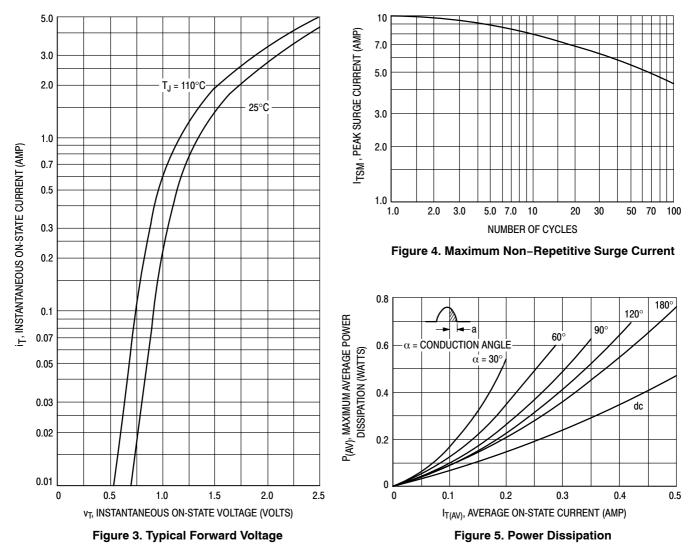
Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak on State Voltage
Ι _Η	Holding Current

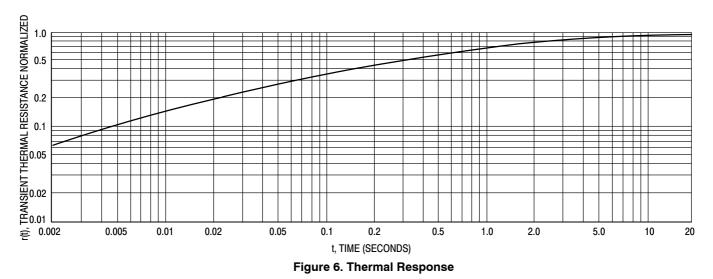


CURRENT DERATING

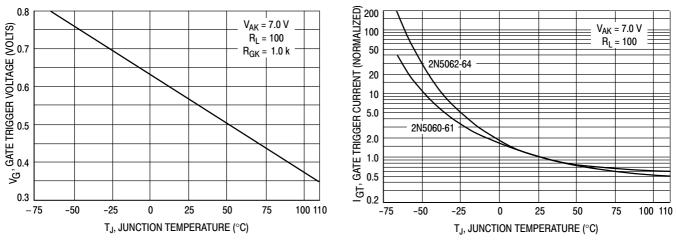




CURRENT DERATING

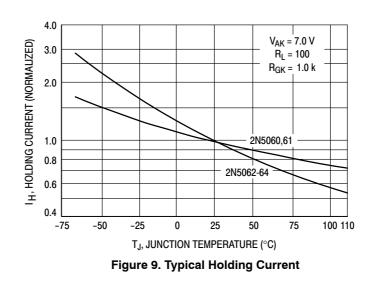












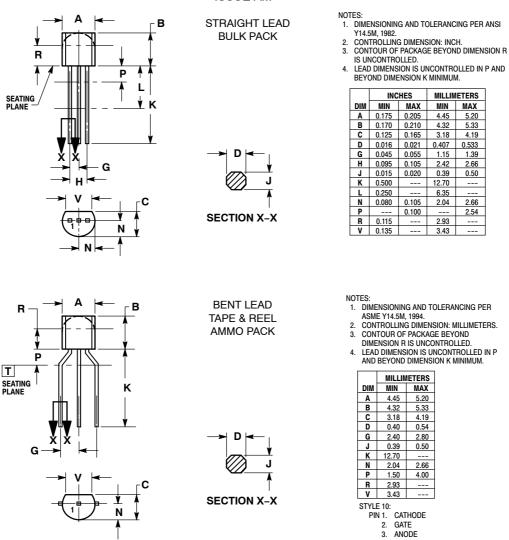
ORDERING INFORMATION

Device	Package	Shipping [†]
2N5060G	TO-92 (Pb-Free)	5000 Units / Box
2N5060RLRA	TO-92	2000 / Tape & Reel
2N5060RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5060RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N5061G	TO-92 (Pb-Free)	5000 Units / Box
2N5061RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5062G	TO-92 (Pb-Free)	5000 Units / Box
2N5062RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5064RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N5064RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5064G	TO-92 (Pb-Free)	5000 Units / Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILIC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILIC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILIC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILIC obsent or any liability nor the rights of others. SCILIC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other applications. intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

For additional information, please contact your local

Order Literature: http://www.onsemi.com/orderlit

Sales Representative

2N5060/D

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SCRs category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

NTE5428 NTE5448 NTE5457 NTE5511 T1500N16TOF VT T720N18TOF T880N14TOF T880N16TOF TS110-7UF TT104N12KOF-A TT104N12KOF-K TT162N16KOF-A TT162N16KOF-K TT330N16AOF VS-16RIA100 VS-22RIA20 VS-2N5206 VS-2N685 VS-40TPS08A-M3 VS-ST230S12P1VPBF 057219R CLB30I1200HB T1190N16TOF VT T1220N22TOF VT T201N70TOH T830N18TOF TD92N16KOF-A TT250N12KOF-K VS-2N692 VS-2N689 VS-25RIA40 VS-16RIA120 VS-10RIA120 VS-30TPS08PBF NTE5427 NTE5442 VS-2N690 VS-ST300S20P0PBF TT251N16KOF-K VS-22RIA100 VS-16RIA40 CR02AM-8#F00 VS-ST110S12P0VPBF TD250N16KOF-A VS-ST110S16P0 VS-10RIA10 VS-16TTS08-M3 TS110-7A1-AP T930N36TOF VT T2160N24TOF VT